Abstracts

Direct extraction of a distributed nonlinear FET model from pulsed I-V/pulsed S-parameter measurements

In this work, a method for the direct extraction of a field-effect transistor (FET) distributed model is presented. This technique makes use of both pulsed I-V and pulsed S-parameter measurements. Results given are very efficient, especially in terms of time computation and uniqueness. Using this method, the distributed model provides a reliable mean of describing the FET's distributive nature.

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